Abstract :

The influence of isochronal and isothermal annealing for 0 to 180 minutes and at 27

To, 250 0C respectively on the optical and electrical properties of thin films of Sb2S3 have been investigated . The film deposited on glass substrate by thermal vacuum evaporation

Have amorphous structure ,but after annealing at temperature above 2000C for 3 hours

Change to polycrystalline structure . The optical absorption coefficient becomes higher

For subgap absorption at higher annealing temperatures. The value of optical Tauc gap

Changed with the annealing temperature. The Dark electrical resistivity showed a decrease

By about an order of magnitude when increasing both the isochronal and isothermal annealing treatment.